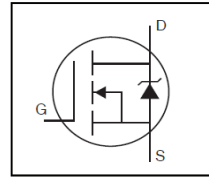


- Logic –Level Gate Drive
- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free

HEXFET® Power MOSFET



V_{DSS}	100V
R_{DS(on)}	0.18Ω
I_D	8.1A



TO-220 Full-Pak

G	D	S
Gate	Drain	Source

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 Full Pak eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heat sink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heat sink using a single clip or by a single screw fixing.

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLI520NPbF	TO-220 Full-Pak	Tube	50	IRLI520NPbF

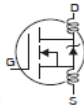
Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	8.1	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	5.7	
I _{DM}	Pulsed Drain Current ①⑥	35	
P _D @ T _C = 25°C	Maximum Power Dissipation	30	W
	Linear Derating Factor	0.20	W/°C
V _{GS}	Gate-to-Source Voltage	± 16	V
E _{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②⑥	85	mJ
I _{AR}	Avalanche Current ①⑥	6.0	A
E _{AR}	Repetitive Avalanche Energy ①	3.0	mJ
dv/dt	Peak Diode Recovery dv/dt③⑥	5.0	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

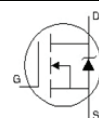
Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	5.0	°C/W
R _{θJA}	Junction-to-Ambient	—	65	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

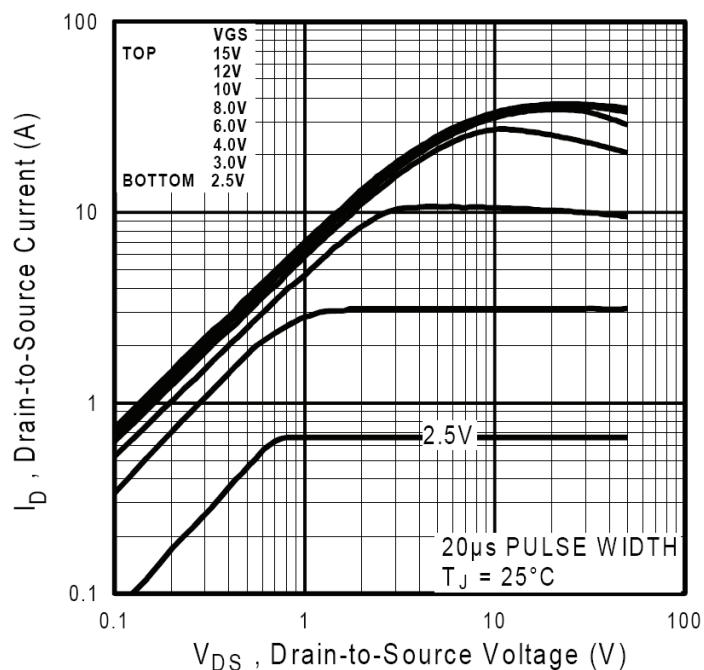
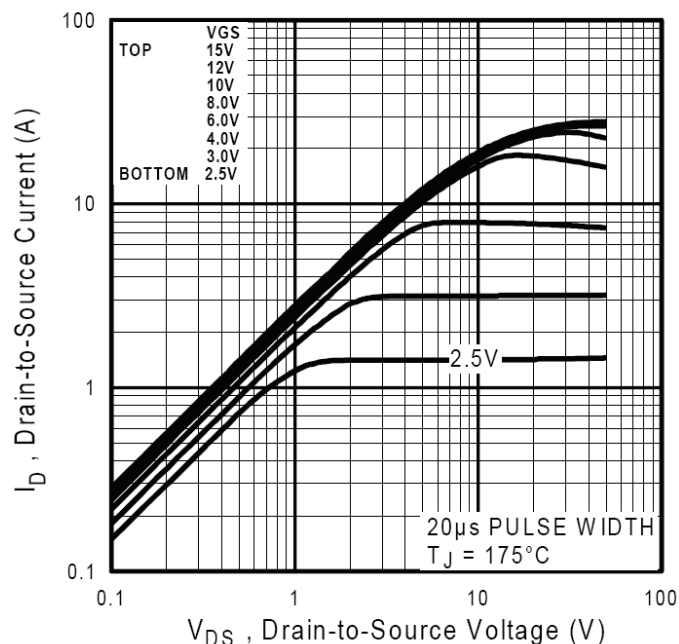
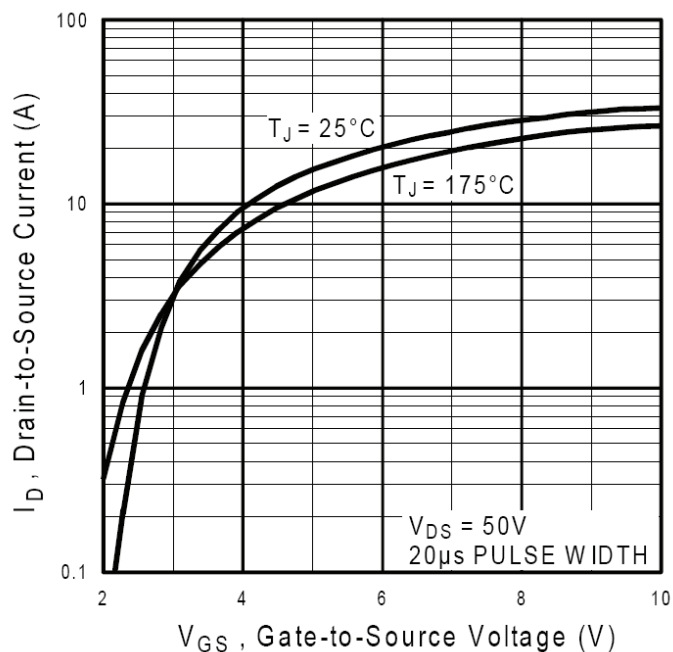
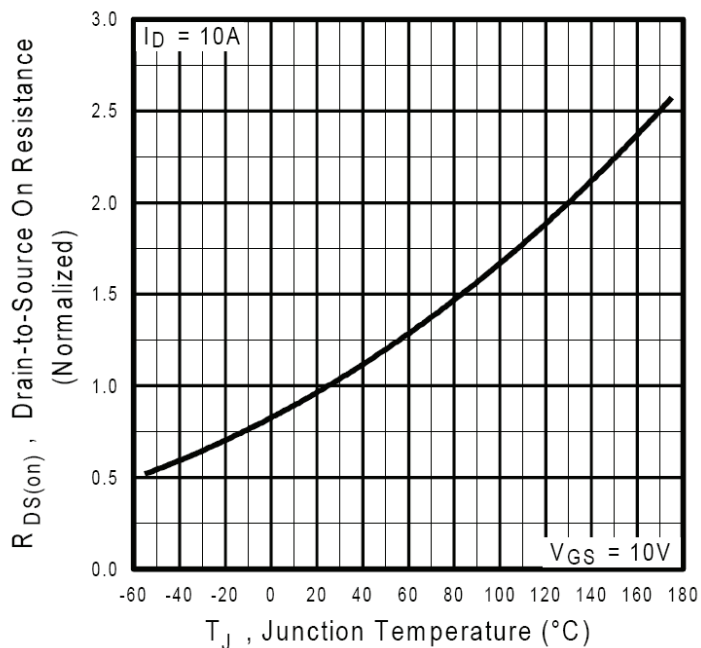
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$ ⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.18	Ω	$V_{GS} = 10V, I_D = 6.0A$
		—	—	0.22		$V_{GS} = 5.0V, I_D = 6.0A$
		—	—	0.26		$V_{GS} = 4.0V, I_D = 5.0A$
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Trans conductance	3.1	—	—	S	$V_{DS} = 25V, I_D = 6.0A$ ⑥
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	20	nC	$I_D = 6.0A$
Q_{gs}	Gate-to-Source Charge	—	—	4.6		$V_{DS} = 80V$
Q_{gd}	Gate-to-Drain Charge	—	—	10		$V_{GS} = 5.0V$, See Fig. 6 and 13 ④ ⑥
$t_{d(on)}$	Turn-On Delay Time	—	40	—		$V_{DD} = 50V$
t_r	Rise Time	—	35	—	ns	$I_D = 6.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	23	—		$R_G = 11\Omega, V_{GS} = 5.0V$
t_f	Fall Time	—	22	—		$R_D = 8.2\Omega$, See Fig. 10 ④ ⑥
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	440	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	97	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	50	—		$f = 1.0\text{MHz}$, See Fig. 5 ⑥
C	Drain to Sink Capacitance	—	12	—		$f = 1.0\text{MHz}$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	8.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ① ⑥	—	—	35		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 6.0A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	110	160	ns	$T_J = 25^\circ\text{C}, I_F = 6.0A$
Q_{rr}	Reverse Recovery Charge	—	410	620	nC	$di/dt = 100A/\mu s$ ④ ⑥
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 4.7\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 6.0A$ (See fig. 12)
- ③ $I_{SD} \leq 6.0A$, $di/dt \leq 340A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ $t = 60s$, $f = 60\text{Hz}$
- ⑥ Uses IRL520N data and test conditions.


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

Fig. 3 Typical Transfer Characteristics

Fig. 4 Normalized On-Resistance vs. Temperature

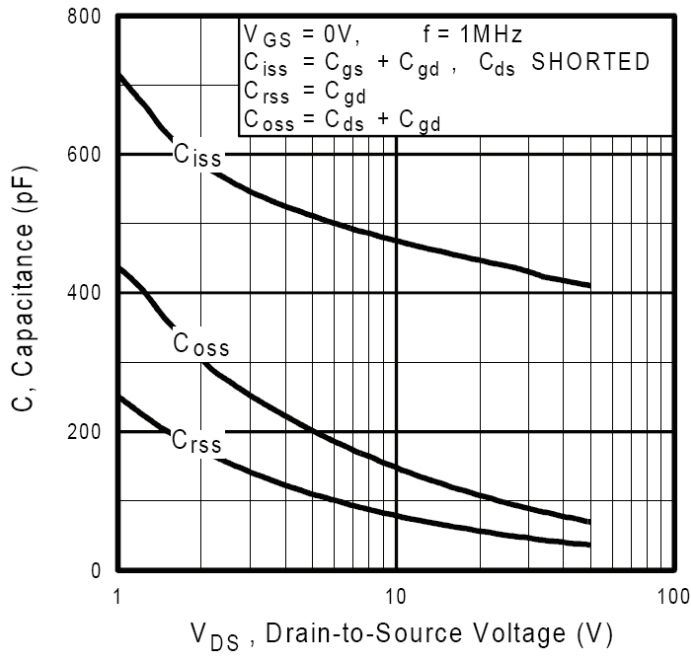


Fig 5. Typical Capacitance vs.
Drain-to-Source Voltage

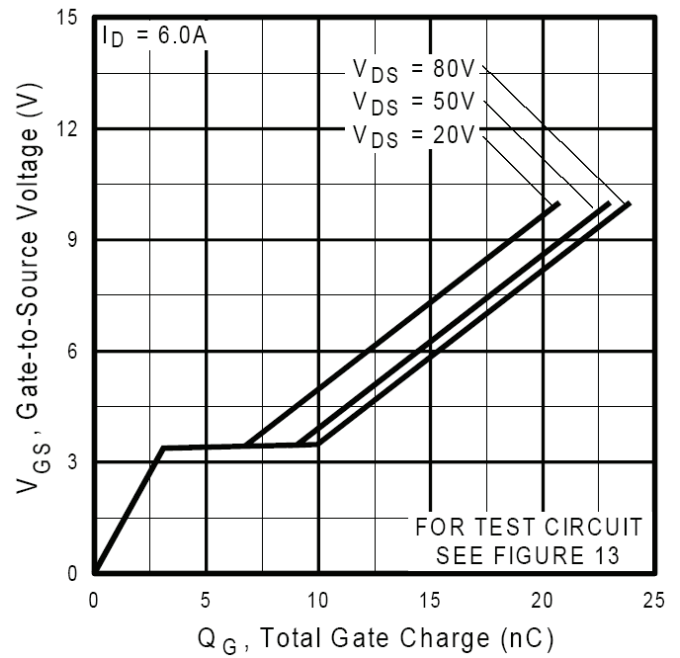


Fig 6. Typical Gate Charge vs.
Gate-to-Source Voltage

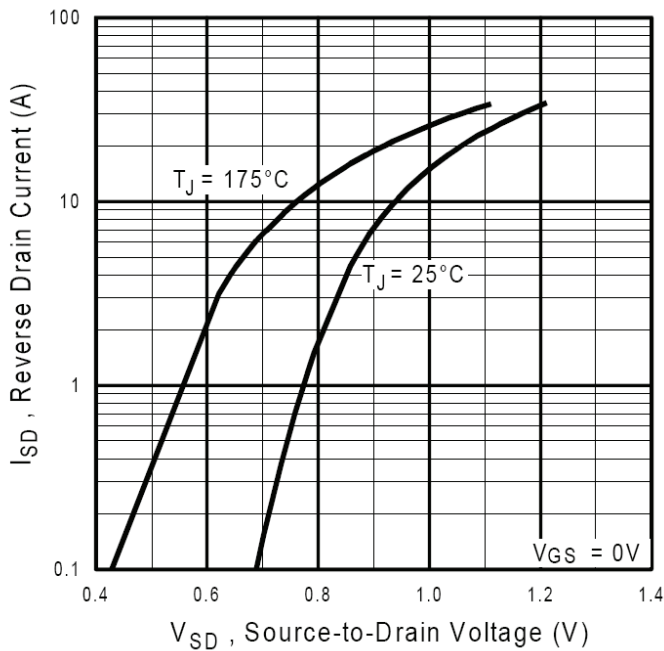


Fig. 7 Typical Source-to-Drain Diode
Forward Voltage

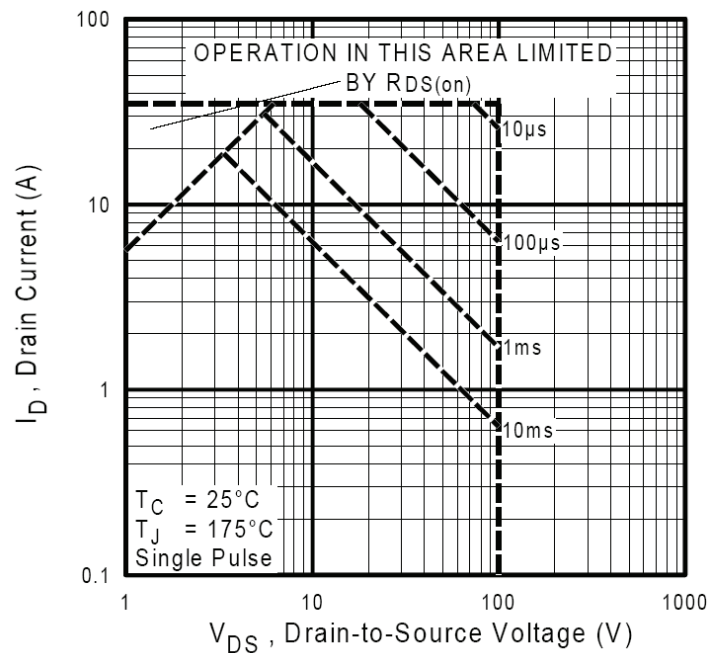


Fig 8. Maximum Safe Operating Area

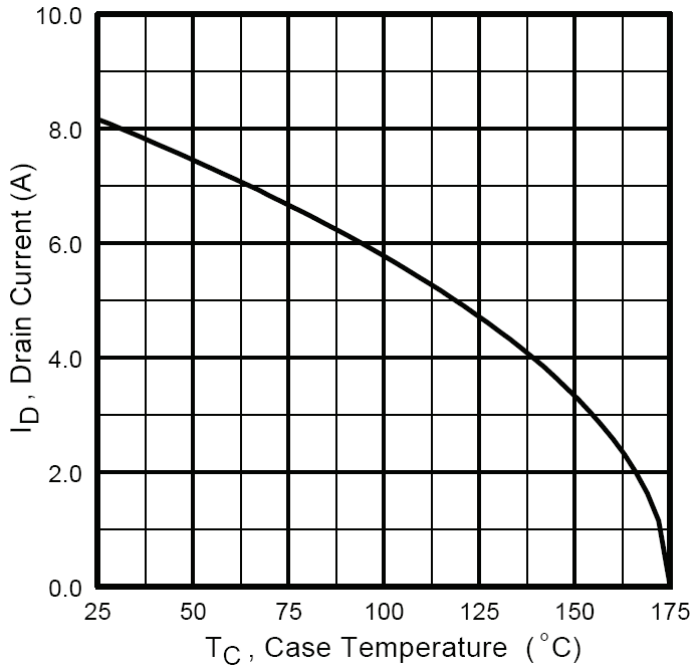


Fig 9. Maximum Drain Current vs. Case Temperature

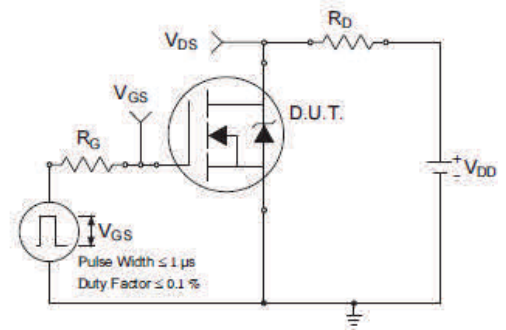


Fig 10a. Switching Time Test Circuit

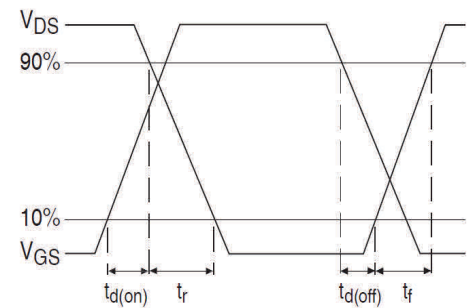


Fig 10b. Switching Time Waveforms

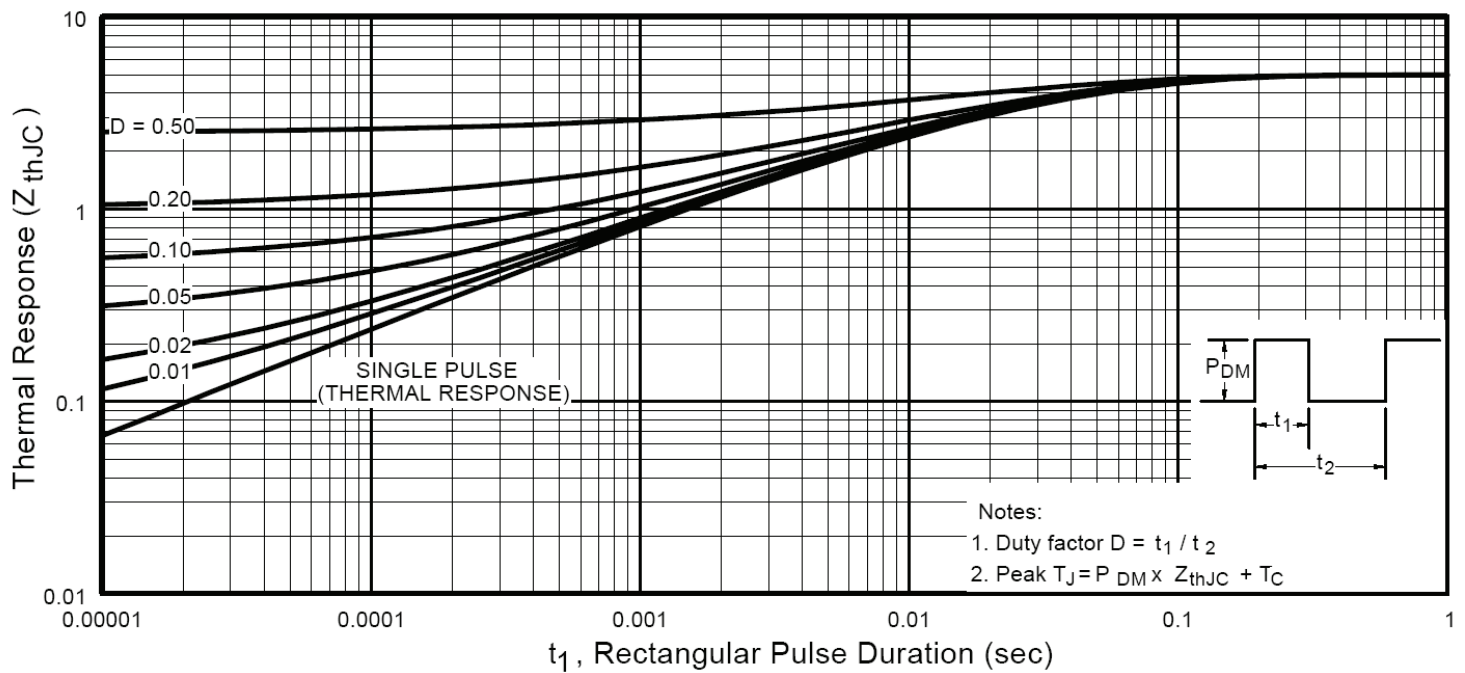


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

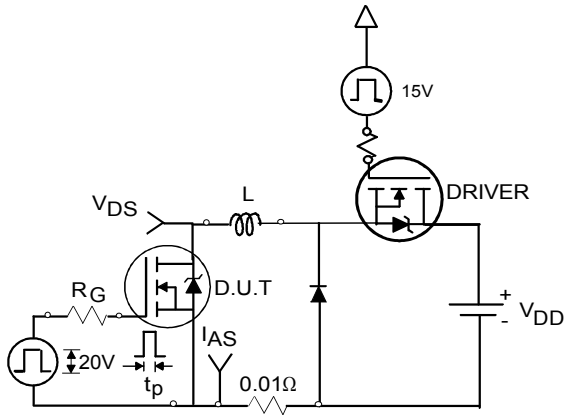


Fig 12a. Unclamped Inductive Test Circuit

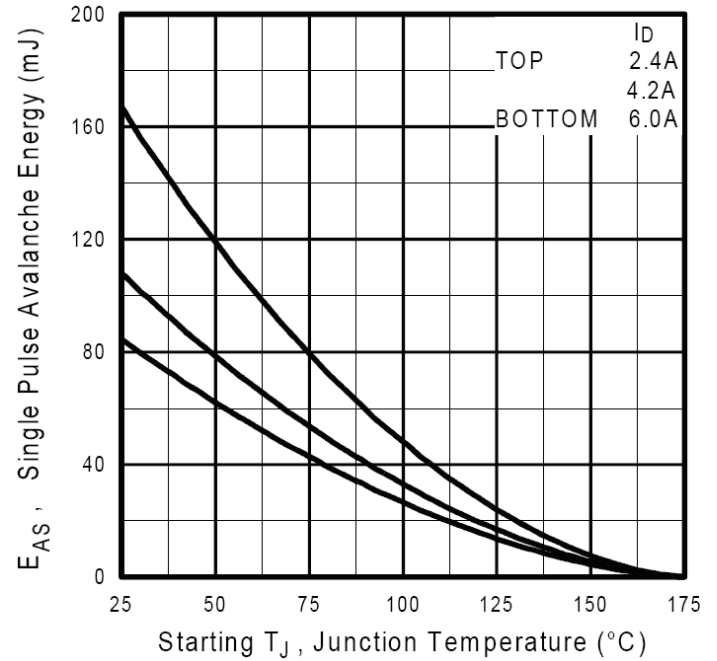


Fig 12c. Maximum Avalanche Energy vs. Drain Current

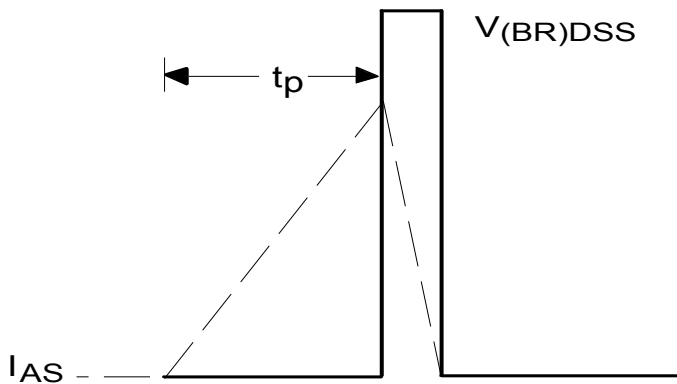


Fig 12b. Unclamped Inductive Waveforms

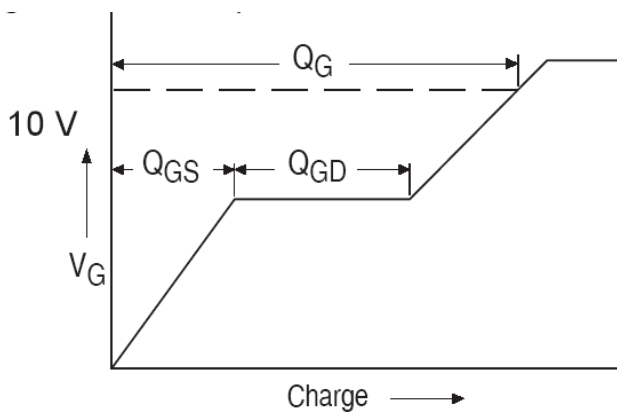


Fig 13a. Gate Charge Waveform

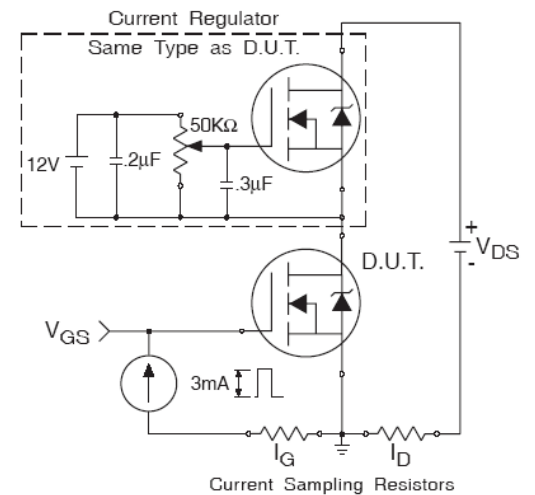


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

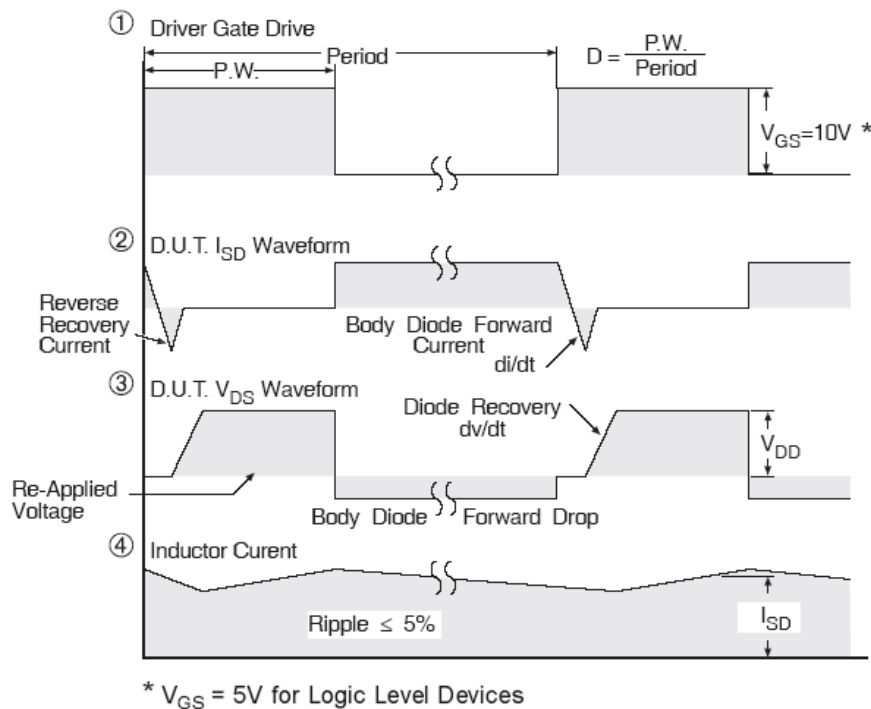
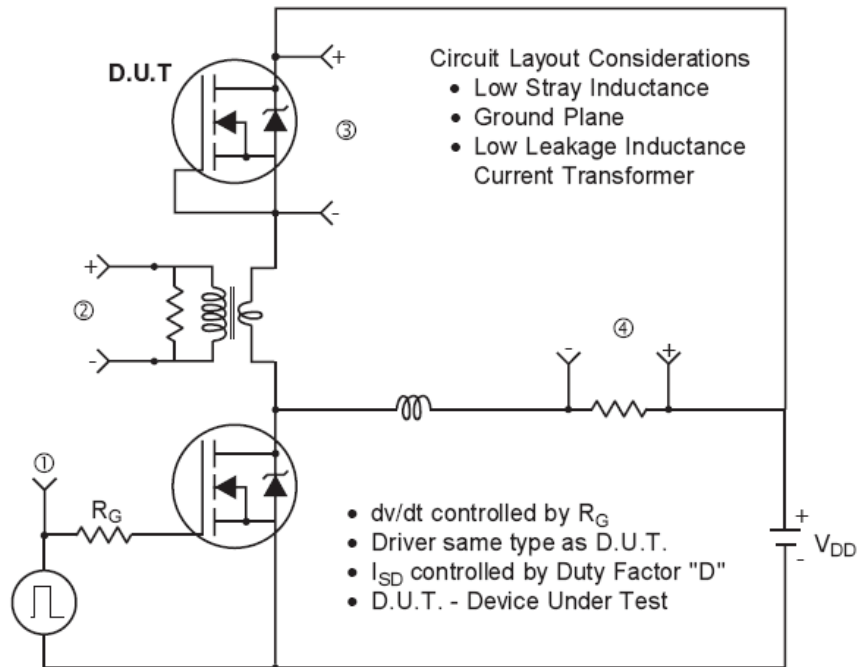
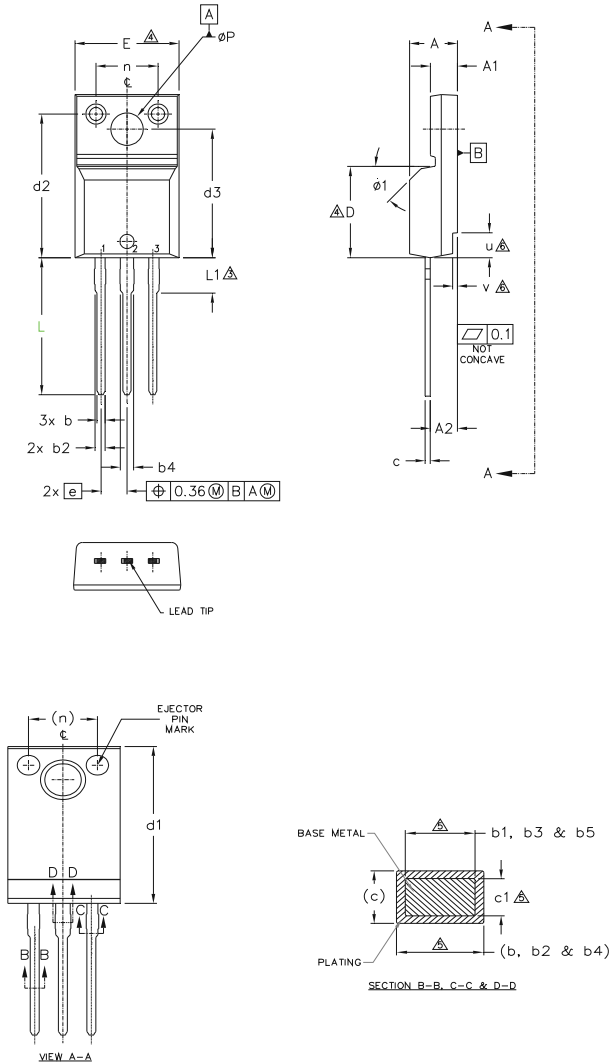


Fig 14. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

TO-220 Full-Pak Package Outline (Dimensions are shown in millimeters (inches))


Qualification Information

Qualification Level	Industrial (per JEDEC JESD47F) [†]	
Moisture Sensitivity Level	TO-220 Full-Pak	N/A
RoHS Compliant	Yes	

[†] Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Comments
4/27/17	- Changed datasheet with Infineon logo - all pages. - Corrected Package Outline on page 8. - Added disclaimer on last page.

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